layer dielectric film, **9** NiSi layer, **10** Source electrode, **11** Gate electrode pad (Gate electrode), **12** Field oxide film, **13** JTE layer, **14** p-type semiconductor layer, **15** p-type semiconductor substrate, **16** Emitter electrode, **17** Drain electrode, **18** Collector electrode.

1.-**9**. (canceled)

10. A silicon carbide semiconductor device comprising:

a silicon carbide semiconductor substrate;

a drift layer of a first conductivity type provided on a main surface of said silicon carbide semiconductor substrate;

a first well layer of a second conductivity type provided from an upper surface of said drift layer to an inner part of said drift layer and provided in a cell region in which a plurality of cells each functioning as a semiconductor element are formed, and a second well layer of a second conductivity type provided in a periphery of said cell region;

a semiconductor layer of said second conductivity type provided in an upper layer of said second well layer;

a gate insulating film and a filed oxide film provided on said semiconductor layer;

a gate electrode provided on said gate insulating film and said field oxide film; and

a gate electrode pad provided immediately above said gate electrode.

11. The silicon carbide semiconductor device according to claim **10**, wherein

said drift layer, said first well layer, said second well layer, and said semiconductor layer are formed of silicon carbide.

12. The silicon carbide semiconductor device according to claim **10**, wherein

said semiconductor layer is formed in a comb teeth-like shape in plan view in said second well layer.

13. The silicon carbide semiconductor device according to claim **11**, wherein

said semiconductor layer is formed in a comb teeth-like shape in plan view in said second well layer.

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